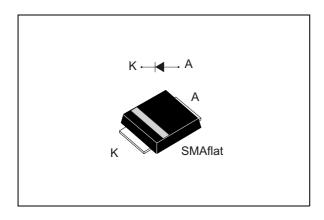


Power Schottky rectifier

Datasheet - production data



Features

- · Negligible switching losses
- · High junction temperature capability
- · Very small conduction losses
- Low leakage current
- Avalanche rated
- ECOPACK[®] compliant component
- T_i = -40 °C minimum operating

Description

The STPS2170 is a 170 V Schottky rectifier suited for switch mode power supplies and high frequency DC to DC converters.

Packaged in SMAflat, this device is especially intended for use in low voltage, high frequency inverters, freewheeling and polarity protection. Also ideal for all LED lighting applications where efficiency and space constraint are required.

Table 1. Device summary

Symbol	Value
I _{F(AV)}	2 A
V_{RRM}	170 V
V _F (typ)	0.62 V
T _j (max)	175 °C

Characteristics STPS2170

1 Characteristics

Table 2. Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Parameter	Value	Unit	
V _{RRM}	Repetitive peak reverse voltage	170	V	
V _{RRM}	Repetitive peak reverse voltage, T _j = -40 °C	160	V	
I _{F(RMS)}	Forward rms current	15	Α	
I _{F(AV)}	Average forward current, δ = 0.5, square wave SMAflat, T _L = 145 °C		2	А
I _{FSM}	Surge non repetitive forward current	70	А	
P _{ARM} ⁽¹⁾	Repetitive peak avalanche power, square wave	165	W	
T _{stg}	Storage temperature range		-65 to +175	°C
Tj	Operating junction temperature ⁽²⁾	-40 to +175	°C	

For pulse time duration deratings, please refer to Figure 3. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the STMicroelectronics Application notes AN1768, "Admissible avalanche power of Schottky diodes" and AN2025, "Converter improvement using Schottky rectifier avalanche specification".

Table 3. Thermal parameters

Symbol	Parameter	Value	Unit
R _{th(j-l)}	Junction to lead, SMAflat	20	°C/W

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾ Reverse leakage curr	Poverse leekage gurrent	T _j = 25 °C	W - W			2.8	μΑ
	Treverse leakage current	$T_j = 125 \text{ °C}$ $V_R = V_{RRM}$		0.5	2.8	mA	
V _F ⁽²⁾ Forward		T _j = 25 °C	I _F = 2 A			0.82	
	Forward voltage drop	T _j = 125 °C			0.62	0.67	V
		T _j = 25 °C	I _F = 4 A			0.89	'
		T _j = 125 °C			0.70	0.75	

^{1.} Pulse test: $t_p = 5$ ms, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.59 \text{ x } I_{F(AV)} + 0.04 \text{ x } I_{F}^{2}_{(RMS)}$$

^{2.} $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

^{2.} Pulse test: t_p = 380 μ s, δ < 2%

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Figure 1. Average forward power dissipation versus average forward current

 $P_{F(AV)}(W)$

2.0

1.6

1.2

0.8

0.0

0.0

0.4

8.0

 $\delta = 0.05 - \delta = 0.1 - \delta = 0.2 - \delta = 0.5 - \delta = 1.$ $\delta = tp/T \rightarrow tp \qquad l_{F(AV)}(A)$

1.6

2.0

Figure 2. Average forward current versus ambient temperature ($\delta = 0.5$)

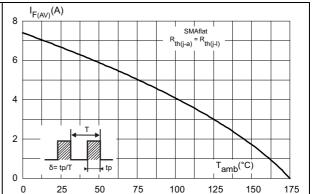
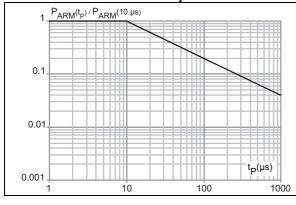


Figure 3. Normalized avalanche power derating versus pulse duration (pulse > 10 μ s, T_i < 150 °C)

1.2

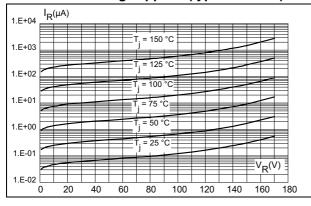
Figure 4. Relative variation of thermal impedance junction to lead versus pulse duration

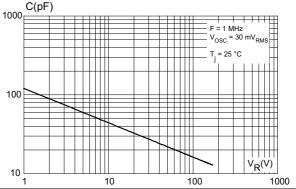


 $Z_{th(j-l)}/R_{th(j-l)}$ 1.0 0.9 0.8 0.7 0.6 0.5 0.4 0.3 Single pulse 0.2 0.1 t_P(s) 0.0 1.E-04 1.E-01 1.E-03 1.E-02 1.E+00

Figure 5. Reverse leakage current versus reverse voltage applied (typical values)

Figure 6. Junction capacitance versus reverse voltage applied (typical values)





Characteristics STPS2170

Figure 7. Forward voltage drop versus forward Figure 8. Forward voltage drop versus forward current (typical values) current (maximum values)

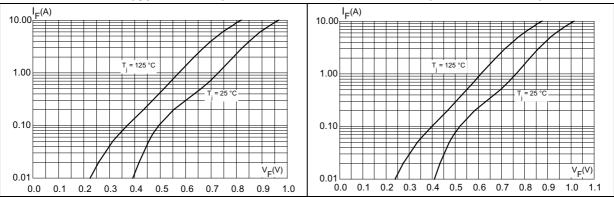
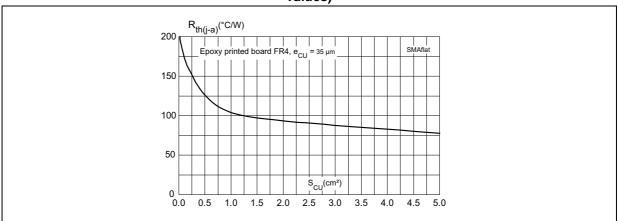


Figure 9. Thermal resistance junction to ambient versus copper surface under each lead (typical values)



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2 Package information

- Epoxy meets UL94,V0
- Lead-free package
- · Band indicates cathode

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

E E1

L2x

L2x

L2x

L12x

Figure 10. SMAflat dimensions definitions

Package information STPS2170

Table 5. SMAflat dimension values

	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	0.90		1.10	0.035		0.043
b	1.25		1.65	0.049		0.065
С	0.15		0.40	0.006		0.016
D	2.25		2.95	0.088		0.116
Е	4.80		5.60	0.189		0.220
E1	3.95		4.60	0.156		0.181
L	0.75		1.50	0.030		0.059
L1		0.50			0.019	
L2		0.50			0.019	

Figure 11. SMAflat footprint, dimensions in mm (inches)

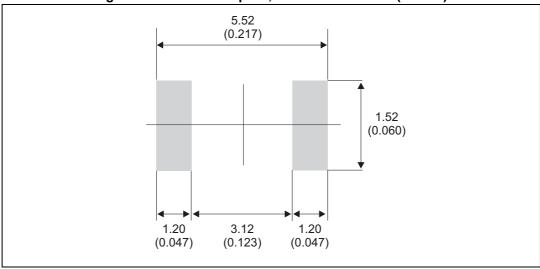
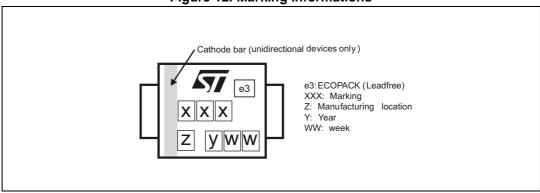


Figure 12. Marking informations



3 Ordering information

Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS2170AF	F2170	SMAflat	0.035 g	10000	Tape and reel

4 Revision history

Table 7. Document revision history

Date		Revision	Changes
14-Oct-201	4	1	First release.

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